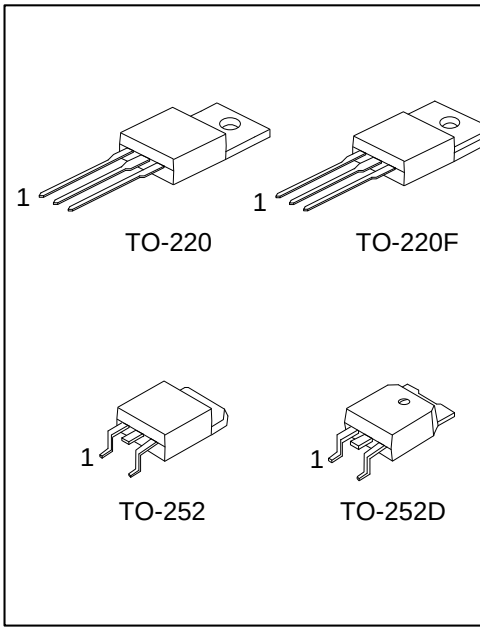
UTT70N06

Power MOSFET

70 Amps, 60 Volts
N-CHANNEL POWER MOSFET



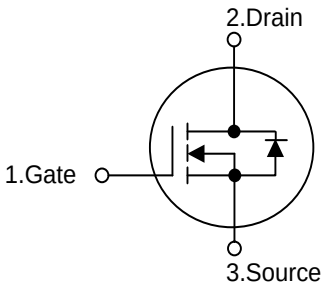
■ DESCRIPTION

The UTC **UTT70N06** is N-channel enhancement mode power field effect transistors with stable off-state characteristics, fast switching speed, low thermal resistance, usually used at telecom and computer application.

■ FEATURES

* $R_{DS(ON)}$ ≤ 15 mΩ @ V_{GS}=10V, I_D=35A
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability

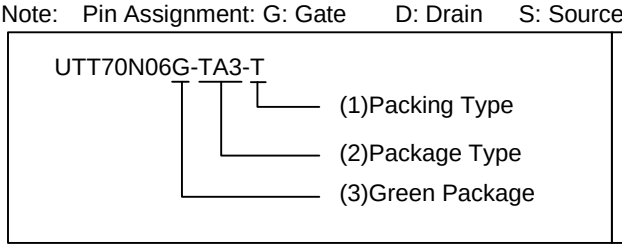
■ SYMBOL



■ ORDERING INFORMATION

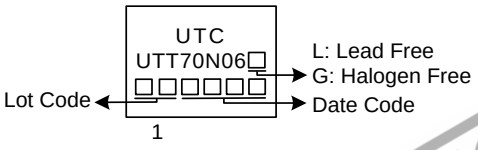
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT70N06L-TA3-T	UTT70N06G-TA3-T	TO-220	G	D	S	Tube
UTT70N06L-TF3-T	UTT70N06G-TF3-T	TO-220F	G	D	S	Tube
UTT70N06L-TN3-R	UTT70N06G-TN3-R	TO-252	G	D	S	Tape Reel
UTT70N06L-TND-R	UTT70N06G-TND-R	TO-252D	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TN3: TO-252, TND: TO-252D
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	T_C = 25°C	I_D	70	A
	T_C = 100°C		56	A
Drain Current Pulsed (Note 2)		I_{DM}	280	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	80	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	10	V/ns
Power Dissipation	TO-220	P_D	104	W
	TO-220F		36	W
	TO-252/TO-252D		50	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repeativity rating: pulse width limited by junction temperature.
3. L=0.1mH, I_{AS}=40A, V_{DD}=25V, R_G=20Ω, Starting T_J=25°C
4. I_{SD}≤48A, di/dt≤300A/μs, V_{DD}≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

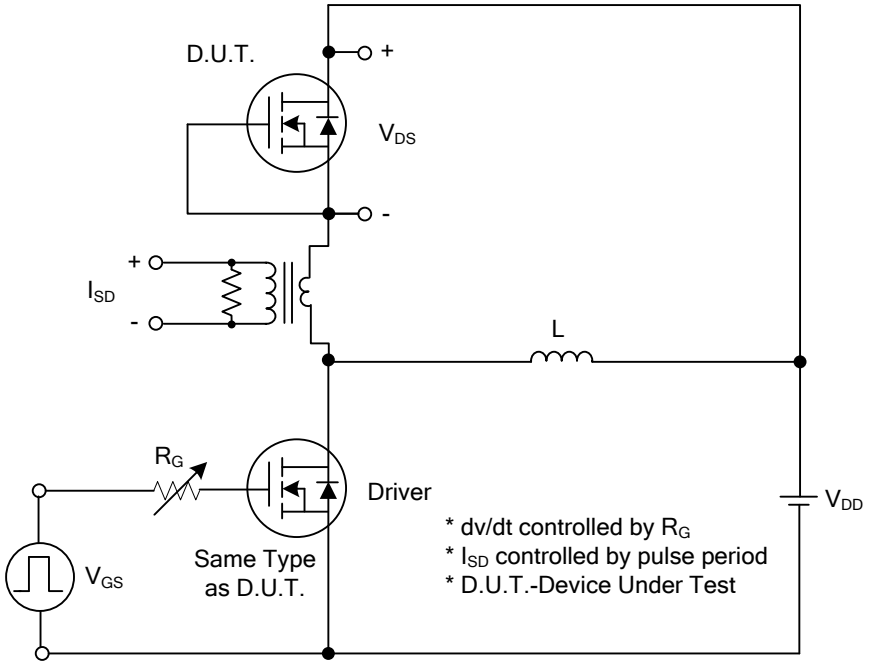
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	°C/W
	TO-252/TO-252D		100	°C/W
Junction to Case	TO-220	θ_{JC}	1.2	°C/W
	TO-220F		3.47	°C/W
	TO-252/TO-252D		2.5	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C =25°C, unless otherwise specified)

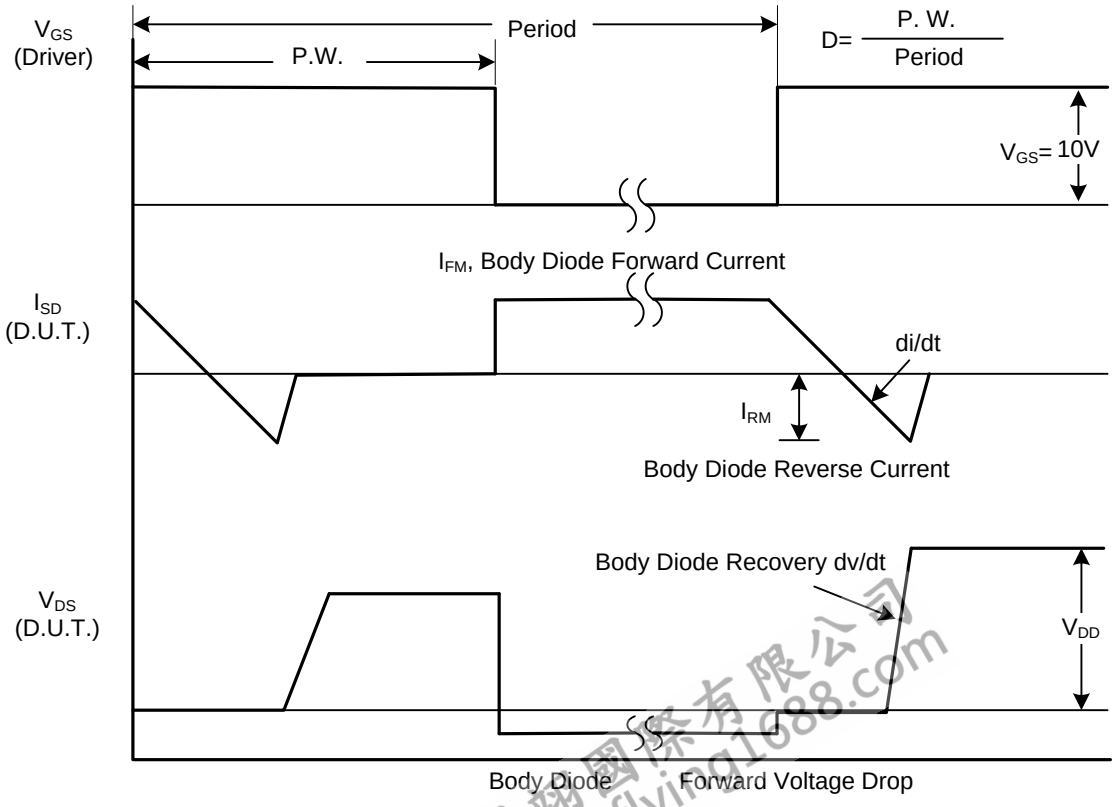
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=20V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\triangle T_J$	I_D = 1mA, Referenced to 25°C		0.08		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=35A			15	mΩ
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1MHz		3500		pF
Output Capacitance		C_{OSS}			310		pF
Reverse Transfer Capacitance		C_{RSS}			55		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS}=50V, V_{GS}=10V, I_D=48A, I_G=100μA (Note 1, 2)		275		nC
Gate-Source Charge		Q_{GS}			18		nC
Gate-Drain Charge (Miller Charge)		Q_{GD}			41		nC
Turn-On Delay Time		$t_{D(ON)}$	V_{DD}=30V, V_{GS}=10V,I_D=0.5A (Note 1, 2)		125		ns
Turn-On Rise Time		t_R			160		ns
Turn-Off Delay Time		$t_{D(OFF)}$			720		ns
Turn-Off Fall Time		t_F			200		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				70	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				280	
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_S=70A			1.4	V
Reverse Recovery Time		t_{rr}	V_{GS}=0V, I_S=70A dI$_F$/dt=100A/μs		90		ns
Reverse Recovery Charge		Q_{rr}			300		μC

Notes: 1. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



1A Peak Diode Recovery dv/dt Test Circuit



1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS

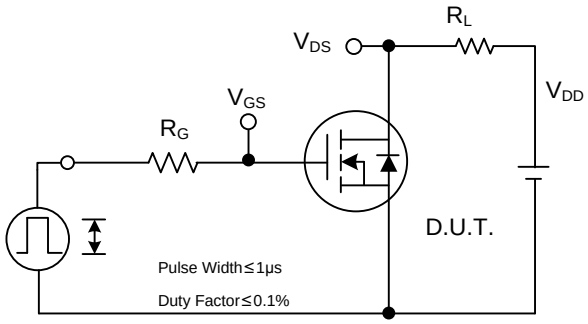


Fig. 2A Switching Test Circuit

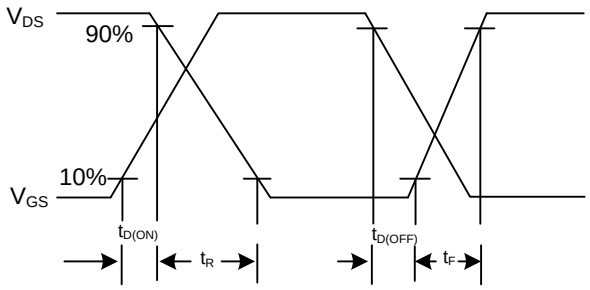


Fig. 2B Switching Waveforms

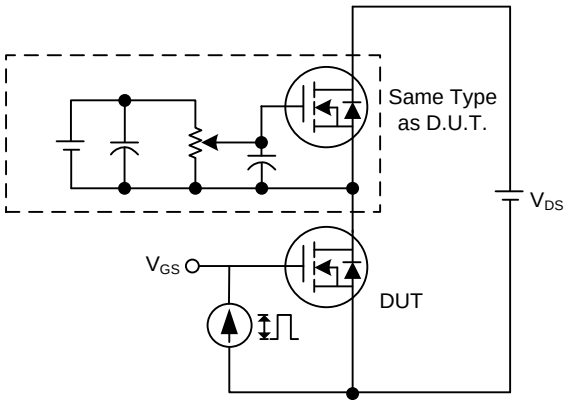


Fig. 3A Gate Charge Test Circuit

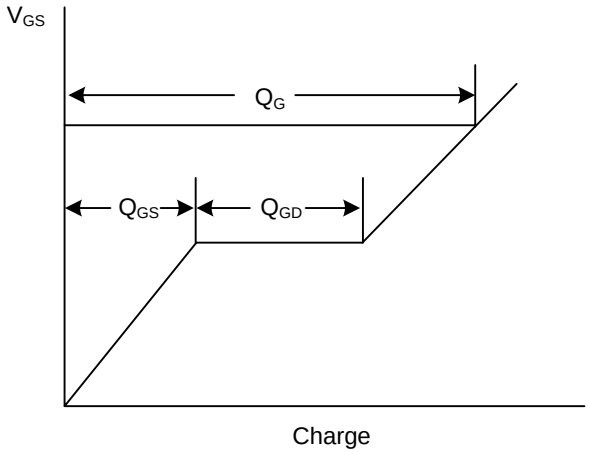


Fig. 3B Gate Charge Waveform

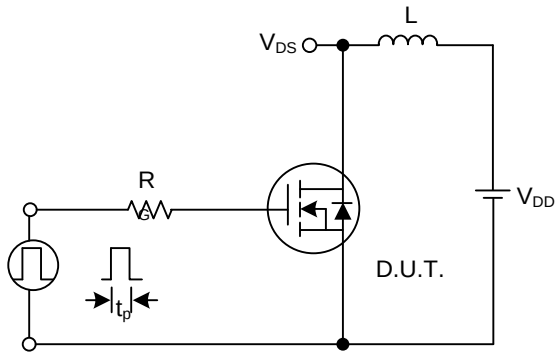


Fig. 4A Unclamped Inductive Switching Test Circuit

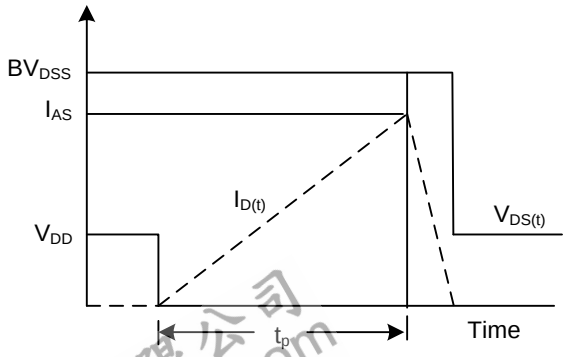


Fig. 4B Unclamped Inductive Switching Waveforms